

ANNOUNCEMENT OF AVAILABILITY: 2" GaN ELOG/SiC EPIWAFERS

As a new product offering, effective June 6, 2004, Cree now has available SiC substrates with a GaN ELOG structure.

The substrates are 2" diameter, 6H, n-type, on-axis that conform with Cree standard product specifications.

The GaN ELOG structure is comprised of an 8 um thick Si-doped GaN layer on a conductive Si-doped AlGaN buffer.

This non-planar structure contains reduced defect areas for LD fabrication, and can be cleaved for formation of LD facets.

The part number for this product is S6NMD0SELOG001-00G2, and material is available for immediate shipment.

Contact Cree for pricing, additional details and delivery.

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